



# FSS174 — P-Channel Silicon MOSFET

## General-Purpose Switching Device Applications

### Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

### Specifications

**Absolute Maximum Ratings** at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-30	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	I <sub>D</sub>		-6	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-24	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (1200mm <sup>2</sup> X0.8mm)	1.6	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

**Electrical Characteristics** at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0V	-30			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V			-1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±16V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-6A	5.4	9		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =-6A, V <sub>GS</sub> =-10V		26	34	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =-4A, V <sub>GS</sub> =-4.5V		42	59	mΩ
	R <sub>DS(on)3</sub>	I <sub>D</sub> =-4A, V <sub>GS</sub> =-4V		49	69	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-10V, f=1MHz		1500		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =-10V, f=1MHz		280		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> =-10V, f=1MHz		250		pF

Marking : S174

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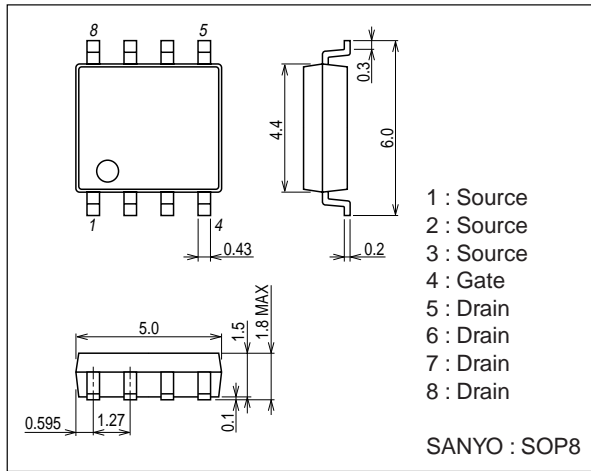
# FSS174

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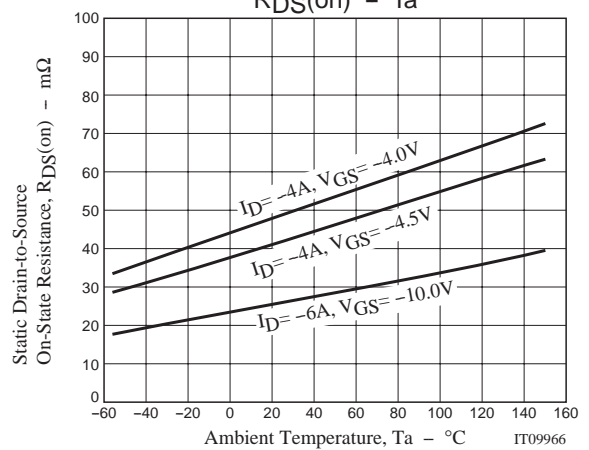
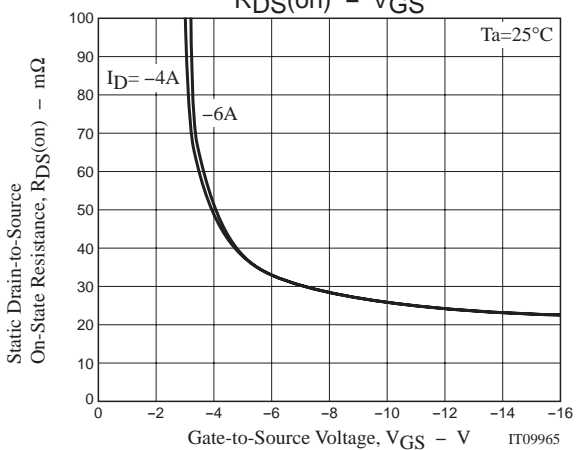
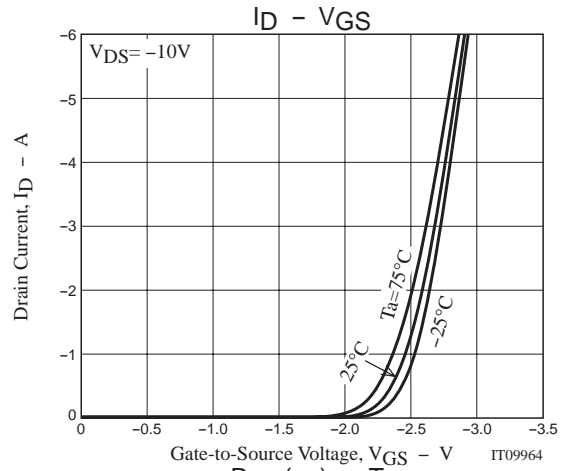
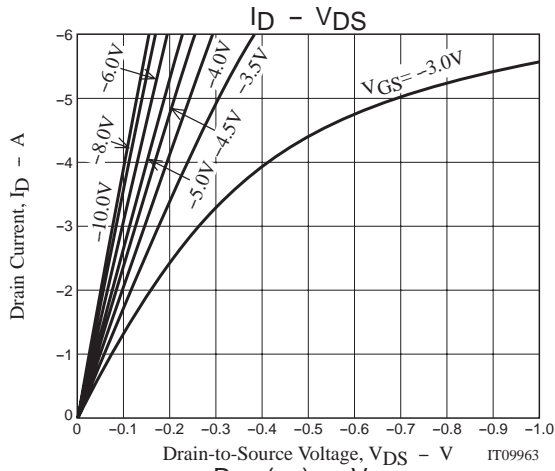
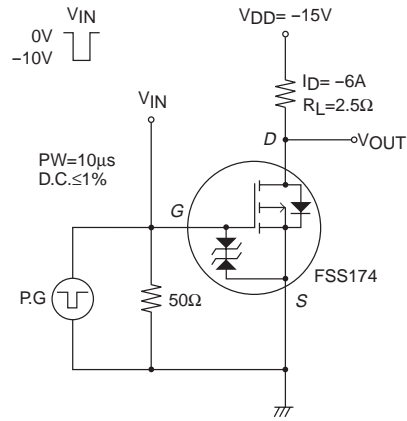
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		15		ns
Rise Time	$t_r$	See specified Test Circuit.		100		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		150		ns
Fall Time	$t_f$	See specified Test Circuit.		95		ns
Total Gate Charge	Qg	$V_{DS}=-10V, V_{GS}=-10V, I_D=-6A$		30		nC
Gate-to-Source Charge	Qgs	$V_{DS}=-10V, V_{GS}=-10V, I_D=-6A$		4.3		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=-10V, V_{GS}=-10V, I_D=-6A$		5.7		nC
Diode Forward Voltage	$V_{SD}$	$I_S=-6A, V_{GS}=0V$		-0.86	-1.5	V

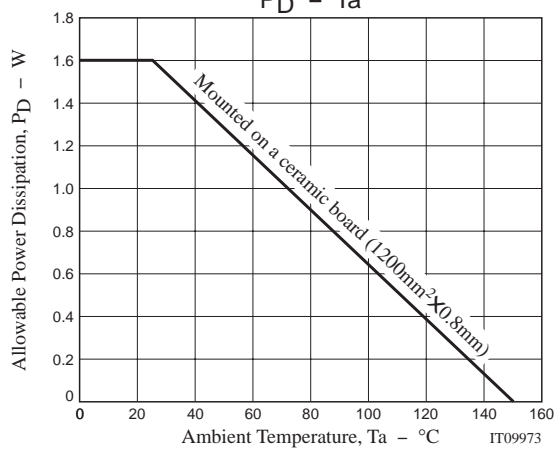
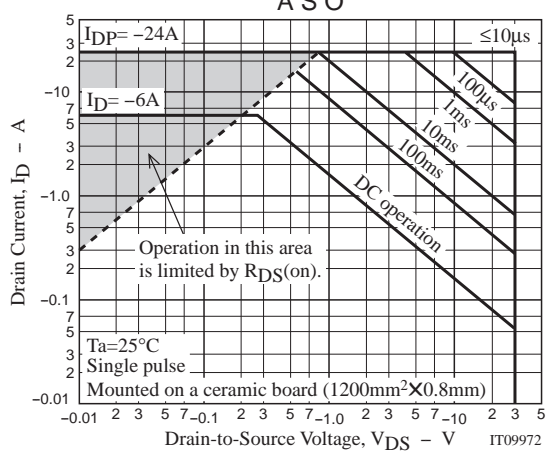
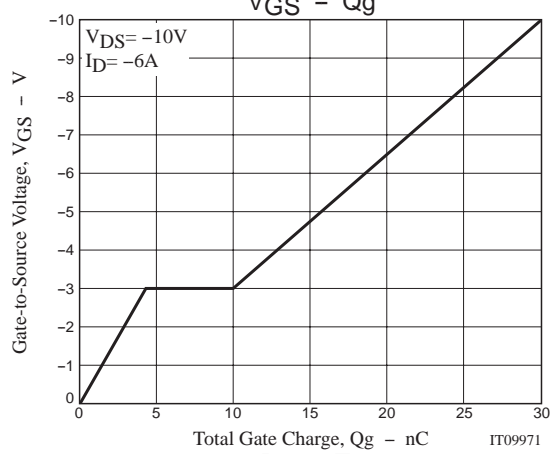
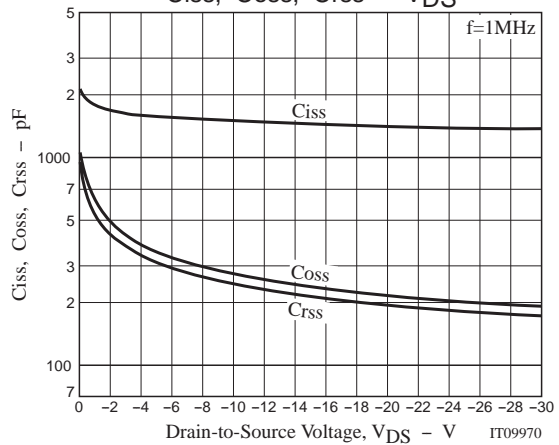
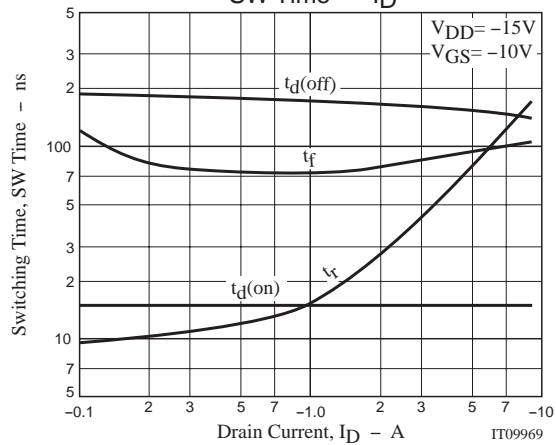
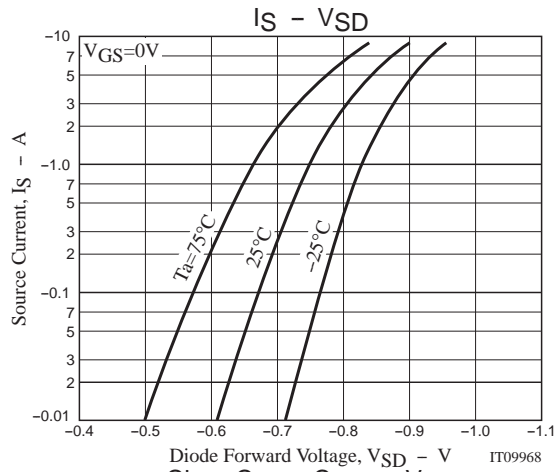
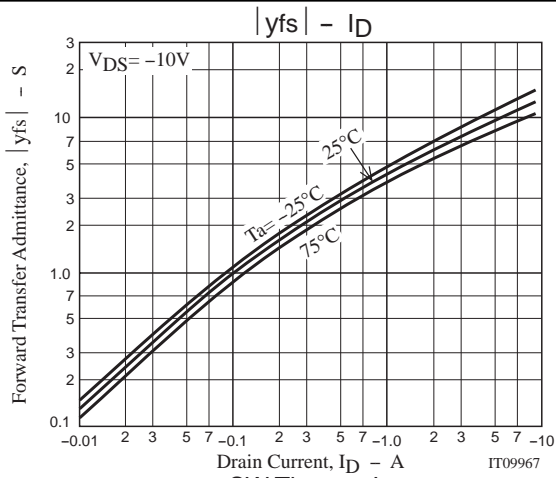
## Package Dimensions

unit : mm  
7005-002



## Switching Time Test Circuit





Note on usage : Since the FSS174 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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